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By: Melod & Ahmberg #8

PATENT AS
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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF:

THOMAS L. RITZDORF ET AL.

APPLICATION No.: 09/885,451

FILED: JUNE 20, 2001

FOR: METHOD AND APPARATUS FOR
LOW TEMPERATURE ANNEALING
OF METALLIZATION MICRO-
STRUCTURES IN THE PRODUCTION
OF A MICROELECTRONIC DEVICE

CONFIRMATION No. 3390

ART UNIT: 1741

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**Information Disclosure Statement Within Three Months of
Application Filing or Before First Action – 37 CFR 1.97(b)**

Commissioner for Patents
Washington, D.C. 20231

Sir:

1. Timing of Submission

This information disclosure is being filed within three months of the filing date of this application or date of entry into the national stage of an international application or before the mailing date of a first Office action on the merits, whichever occurs last [37 CFR 1.97(b)]. The references listed on the enclosed Form PTO-1449 (modified) may be material to the examination of this application; the Examiner is requested to make them of record in the application.

2. Cited Information

☒ Copies of the following references are enclosed:

- ☐ All cited references
- ☐ References marked by asterisks
- ☒ The following:

AHN, E. C. et al. "Adhesion Reliability of Cu-Cr Alloy Films to Polyimide" *Materials Research Society Symposium Proceedings*, 1996, Vol. 427, pp. 141-145, Materials Research Society.

ALERS, G. B. et al. "Trade-off between reliability and post-CMP defects during recrystallization anneal for copper damascene interconnects" *IEEE International Reliability Physics Symposium*, 2001, pp. 350-354.

GLADKIKH, A. *et al.* "Activation Energy of Electromigration in Copper Thin Film Conductor Lines" *Materials Research Society Symposium Proceedings*, 1996, Vol. 427, pp. 121-126, Materials Research Society.

KONONENKO, O. V. *et al.* "Electromigration In Submicron Wide Copper Lines" *Materials Research Society Symposium Proceedings*, 1996, Vol. 427, pp. 127-132, Materials Research Society.

MEI, Y. *et al.* "Thermal Stability and Interaction Between SIOF and Cu Film" *Materials Research Society Symposium Proceedings*, 1996, Vol. 427, pp. 433-439, Materials Research Society.

RUSSELL, S. W. *et al.* "The Effect of Copper on the Titanium-Silicon Dioxide Reaction and the Implications for Self-Encapsulating, Self-Adhering Metallization Lines", *Materials Research Society Symposium Proceedings*, 1992, Vol. 260, pp. 763-768, Materials Research Society, Pittsburgh, PA.

☒ Copies of the following references can be found in parent application Ser. No. 09/018,783:

- ☐ All cited references
- ☒ References marked by asterisks
- ☐ The following:

- ☐ The following references are not in English. For each such reference, the undersigned has enclosed (i) a translation of the reference; (ii) a copy of a communication from a foreign patent office or International Searching Authority citing the reference, (iii) a copy of a reference which appears to be an English-language counterpart, or (iv) an English-language abstract for the reference prepared by a third party. Applicant has not verified that the translation, English-language counterpart or third-party abstract is an accurate representation of the teachings of the non-English reference, though, and reserves the right to demonstrate otherwise.

- ☐ All cited references
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3. Effect of Information Disclosure Statement (37 CFR 1.97(h))

This Information Disclosure Statement is not to be construed as a representation that: (i) a search has been made; (ii) additional information material to the examination of this application does not exist; (iii) the information, protocols, results and the like reported by third parties are accurate or enabling; or (iv) the cited information is, or is considered to be, material to patentability. In addition, applicant does not admit that any enclosed item of information constitutes prior art to the subject invention and specifically reserves the right to demonstrate that any such reference is not prior art.

4. Fee Payment


No fees are believed due. However, should the Commissioner determine that fees are due in order for this Information Disclosure Statement to be considered, the Commissioner is hereby authorized to charge such fees to Deposit Account No. 50-0665.

5. Patent Term Adjustment (37 CFR 1.704(d))

- ☐ The undersigned states that each item of information submitted herewith was cited in a communication from a foreign patent office in a counterpart application and that this communication was not received by any individual designated in 37 C.F.R. § 1.56(c) more than thirty days prior to the filing of this statement. 37 C.F.R. § 1.704(d).

Date: 22 Nov 02

Respectfully submitted,
Perkins Coie LLP



Edward S. Hotchkiss
Registration No. 33,904

Correspondence Address:

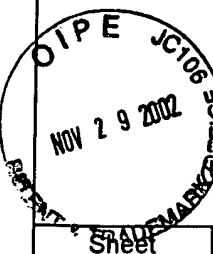
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<div style="display: flex; justify-content: space-between; align-items: center;"> <div style="text-align: left;"> <p>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</p> <p>Form PTO-1449 (Modified)</p> <p>(Use several sheets if necessary)</p> </div> <div style="text-align: right;"> <p>COMPLETE IF KNOWN</p> </div> </div>				Application Number		09/885,451
				Confirmation Number		3390
Filing Date		February 20, 2001				
First Named Inventor		Thomas L. Ritzdorf				
Group Art Unit		1741				
Examiner Name		Unknown				
Attorney Docket No.		29195-8170US2				

1 of 6

U.S. PATENT DOCUMENTS						
Examiner Initials	Cite No.	U.S. Patent or Application		Name of Patentee or Inventor of Cited Document	Date of Publication or Filing Date of Cited Document	Pages, Columns, Lines, Where Relevant Figures Appear
		NUMBER	Kind Code (if known)			
		*2,443,599		Allen E Chester	06/22/48	
		*3,894,918		Corby et al.	07/15/75	
		*4,250,004		Miles et al.	02/10/81	
		*4,539,222		Anderson, Jr. et al.	09/03/85	
		*4,687,552		Early et al.	08/18/87	
		*4,891,069		Holtzman et al.	01/02/90	
		*5,164,332		Kumar	11/17/92	
		*5,314,756		Tagaya	05/24/94	
		*5,431,803		DiFranco et al.	07/11/95	
		*5,600,532		Michiya et al.	02/04/97	
		*5,605,615		Goolsby et al.	02/25/97	
		*5,612,254		Mu et al.	03/18/97	
		*5,627,102		Shinriki et al.	05/06/97	
		*5,893,752		Zhang et al	04/13/99	
		*5,939,788		McTeer	08/17/99	
		*5,969,422		Ting et al.	10/19/99	
		*5,972,192		Dubin et al.	10/26/99	
		*6,001,730		Farkas et al.	12/14/99	
		*6,043,153		Nogami et al.	03/28/00	
		*6,074,544		Reid et al.	06/13/00	
		*6,082,163		Armstrong et al.	06/06/00	
		*6,126,761		DeHaven et al.	10/03/00	
		*6,228,768		Woo et al.	05/08/01	
		*6,254,758		Koyama	07/03/01	
		*6,278,089		Young et al.	08/21/01	
		*6,280,183		Mayur et al.	08/28/01	

EXAMINER	DATE CONSIDERED
<p><small>*EXAMINER: Initial if reference considered, whether or not criteria is in conformance with MPEP 609. Draw line through citation if not in conformance <u>and</u> not considered. Include copy of this form with next communication to application(s).</small></p>	

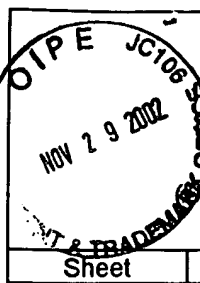
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Sheet	2	of	6

U.S. PATENT DOCUMENTS				
		U.S. Patent or Application		
		*6,297,154	Gross et al.	10/02/01

FOREIGN PATENT DOCUMENTS								
Examiner Initial	Cite No.	Foreign Patent or Application			Name of Patentee or Applicant of Cited Document	Date of Publication or Filing Date of Cited Document	Pages, Columns, Lines, Where Relevant Figures Appear	T
		Office	NUMBER	Kind Code (if known)				
		EP	*0 751 567 A2		Intl. Business Machines Corp.	01/02/97		
		EP	*0 881 672 A2		Intl. Business Machines Corp.	12/02/98		
		EP	*0 982 771 A1		Lucent Technologies, Inc.	03/01/00		
		WO	*98/27585		Intl. Business Machines Corp.	06/25/98		

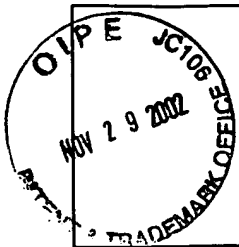
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		RUSSELL, S. W. <i>et al.</i> "The Effect of Copper on the Titanium-Silicon Dioxide Reaction and the Implications for Self-Encapsulating, Self-Adhering Metallization Lines", <i>Materials Research Society Symposium Proceedings</i> , 1992, Vol. 260, pp. 763-768, Materials Research Society, Pittsburgh, PA.	
		*NGUYEN et al, "Inter connect and Contact Metallization," Ried, F. H. and Rathore, G.S. Mathan, C. Plougonven and C.C. Schuckert, PV 97-31, The Electrochemical Society, Inc., Pennington, NJ	

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		*FOULKE, D.G., in "Gold Plating Technology," Reid, F.H. and Goldie, W., p 67, Electrochemical Publicaiton Ltd, British Isle (1996).	
		*TOMOV, V., STOYCHEV, D.S., VITANOVA, I.B., "Recovery And Recrystallization Of Electrodeposited Bright Copper Coatings At Room Temperature. II. X-Ray Investigation Of Primary Recrystallization," <i>Journal of Applied Electrochemistry</i> , 15, 887-894. Chapman and Hall Ltd. (1985).	
		*STOYCHEV, D.S., TOMOV, V., VITANOVA, I.B., "Recovery And Recrystallization Of Electrodeposited Bright Copper Coatings At Room Temperature. I Microhardness in relation to Coating Structure", <i>Journal of Applied Electrochemistry</i> , 15, 879-886. Chapman and Hall Ltd. (1985).	
		*RITZDORF, T., GRAHAM, L., JIN, S., MU, C. and FRASER, D., "Self-Annealing of Electrochemically Deposited Copper Films in Advanced Interconnect Applications," Proceedings of the IEEE 1998 International Interconnect Technology Conference, San Francisco, CA (June 1-3, 1998).	
		*DUBIN, V.M., SHACHAM-DIAMAND, Y., ZHAO, B., VASUDEV, P.K. and TING, C.H., "Sub-Half Micron Electroless Cu Metallization," Materials Research Society Symposium Proceedings, Vol. 427, San Francisco, (1996).	
		*COOK, M. and RICHARDS, T., "The Self-Annealing of Copper," <i>J. Inst. Metals</i> , vol. LXX, pp. 159-173 (1943).	
		*MAK, C.Y., "Electroless Copper Deposition on Metals and Metal Silicides," Materials Research Society Bulletin, (August 1994).	
		*HOGAN, B.M., "Microstructural Stability of Copper Electroplate," (citation unknown but believed to be published more than one year before the date of this patent application).	
		*STOYCHEV, D., VITANOVA, I. VIEWEGER, U., "Influence of the Inclusions in Thick Copper Coatings on Their Physico - Mechanical Properties," (citation unknown but believed to be published more than one year before the date of this patent application).	
		*STOYCHEV, D.S., and AROYO, M.S., 'The Influence of Pulse Frequency on the Hardness of Bright Copper Electrodeposits," <i>Plating & Surface Finishing</i> , pp. 26-28 (August 1997).	
		*STOYCHEV, D.S., and AROYO, M.S., 'On the Influence of Pulse Frequency on the Hardness of Bright Copper Electrodeposits, (citation unknown but believed to be published more than one year before the date of this patent application).	
		*STEIN, B., "A Practical Guide to Understanding, Measuring and Controlling Stress in Electroformed Metals," presented at the AESF Electroforming Symposium, Las Vegas, NV (March 1996).	

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Examiner Name	Unknown
Attorney Docket No.	29195-8170US2

Sheet **4** of **6**

OTHER PRIOR ART-NON PATENT LITERATURE DOCUMENTS

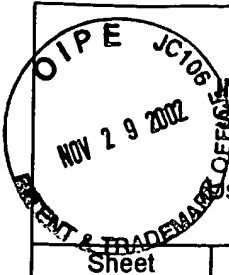
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		*SANCHEZ, J. JR., BESSER, P.R., and FIELD, D.P., "Microstructure of Damascene Processed Al-Cu Interconnects for Integrated Circuit Applications," presented at the Fourth International Workshop on Stress Induced Phenomena in Metallizations, Tokyo, Japan (June 1997).	
		*SANCHEZ, J. JR. and BESSER, P.R., "Modelling Microstructure Development in Trench-Interconnect Structures," Proceedings of the IEEE 1998 International Interconnect Technology Conference, Sunnyvale, CA. (June 1998).	
		*FIELD, D.P., SANCHEZ, J. JR., BESSER, P.R., DINGLEY, D.J., "Analysis of Grain-Boundary Structure in Al-Cu Interconnects," <i>J. Appl. Phys.</i> , 82(5) (September 1, 1997).	
		*GUPTA, D., "Comparative Cu Diffusion Studies in Advanced Metallizations of Cu and Al-Cu Based Thin Films," Materials Research Society Symposium Proceedings, San Francisco, CA (April 1994).	
		*MEGAW, H.D. and STOKES, A.R., "Breadths of X-Ray Diffraction Lines and Mechanical Properties of Some Cold-Worked Metals," <i>J. Inst. Metals</i> , vol. LXXI, pp. 279-289 (1944)	
		*THOMPSON, C.V., and KNOWLTON, B.D., "Designing Circuits and Processes to Optimize Performance and Reliability: Metallurgy Meets Tcad," <i>Microelectronics and Reliability</i> , 36, P. 1683 (1996).	
		*CAREL, R., THOMPSON, C.V., FROST, H.J., <i>Material Research Society Symposium</i> , Vol. 343, Materials Research Society (1994).	
		*FLORO, J.A., CAREL, R. and THOMPSON, C.V., "Energy Minimization During Epitaxial Grain Growth: Strain vs. Interfacial Energy," <i>Material Research Society Symposium</i> , Vol. 317, Materials Research Society, (1994).	
		*PLÖTNER, M., URBANSKY, N., PREUSZ, A. and WENZEL, C., "Control of Mechanical Stresses and their Temperature Dependence in PVD CU Films," presented at Adv. Metalliz. & Interconn. Syst. ULS Applic. San Diego (1997).	
		*WONG, CHEE. C., SMITH, H.I., and THOMPSON, C.V., "Secondary Grain Growth and Graphoepitaxy in Thin Au Films on Submicrometer-Period Gratings," <i>Material Research Society Symposium Proc.</i> , Vol. 47, Materials Research Society (1985).	
		*THOMPSON, C.V., and SMITH, H.I., "Secondary Grain Growth in Thin Films." <i>Material Research Society Symposium Proc.</i> , Vol. 57, Materials Research Society (1987).	

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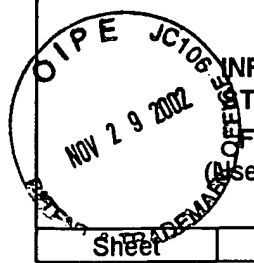
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		*WONG, C.C., SMITH, H.I., and THOMPSON, C.V., "Room Temperature Grain Growth in Thin Au Films, from <i>Grain Boundary Structure and Related Phenomena</i> , supplement to <i>Transactions of Japanese Institute of Metals</i> , 27, p. 641 (1986).	
		*THOMPSON, C.V., "Observations of Grain Growth in Thin Films," from <i>Microstructural Science for Thin Film Metalizations in Electronics Applications</i> , eds. J. Sanchez, D.A. Smith and N. DeLanerolle, The Minerals, Metals & Materials Society (1988).	
		*FROST, H.J., THOMPSON, C.V., and WALTON, D.T., "Abnormal Grain Growth in Thin Films Due to Anisotropy of Free-Surface Energies," <i>Materials Science Forum</i> , Vols. 94-96, pp. 543-550, Trans Tech Publications, Switzerland (1992).	
		*FROST, H.J. and THOMPSON, C.V., "Microstructural Evolution in Thin Films," presented at the Symposium on Computer Simulation of Microstructural Evolution, Toronto, Canada, October 15 (1985).	
		*FROST, H.J. THOMPSON, C.V., and WALTON, D.T., "Grain Growth Stagnation and Abnormal Grain Growth in Thin Films," presented at TMS-AIME Fall Meeting, Indianapolis, IN (1989).	
		*REED-HALL, et al., "Physical Metallurgy Principles," pp. 270, 286 and 287, 83 rd Ed. (1991).	
		*FROST, H.J. and THOMPSON, C.V., "Modeling of Optical Thin Films," reprint from Proceedings of SPIE (International Society for Optical Engineering, San Diego, CA 1987, printed by the Society of Photo-Optical Instrumentation Engineers (1988).	
		*WALTON, D.T., FROST, H.J. and THOMPSON, C.V., "Computer Simulation of Grain Growth in Thin-Film Interconnect Lines," <i>Mat. Res. Soc. Symp. Proc.</i> , vol. 225 (1991).	
		*Harper, J.M.E., Rodbell, K.P., "Microstructure control in semiconductor metallization", <i>J. Vac. Sci. Technol. B</i> 15(4), pp. 763-779, Jul/Aug 1997.	
		*Gangulee, A., "The Structure of Electroplated and Vapor-Deposited Copper Films", <i>J. Appl. Phys.</i> , Vol. 43, No. 3, pp. 867-873, March 1972.	
		*Gangulee, A., "Structure of Electroplated and Vapor-Deposited Copper Films III. Recrystallization and Grain Growth", <i>J. Appl. Phys.</i> , Vol. 45, No. 9, pp. 3749-3756, September 1974.	
		*Gross, M.E. et al, "Microstructure and Texture of Electroplated Copper in Damascene Structures", <i>Material Research Society Proceedings</i> , Vol. 514, 1998.	

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		*Edelstein, D. et al, "Full Copper Wiring in a Sub-0.25µm CMOS ULSI Technology", IEEE, pp. 773-776, 1997.	
		*Ryan, J.G. et al, "Technology Challenges for Advanced Interconnects".	
		*Lowenheim, Frederick, "Electroplating", pp. 416-425, January 1979.	
		*Patent Abstracts of Japan 04-120290, 21 April 1992.	
		*Ahn, E.C., et. al., "Adhesion Reliability of Cu-Cr Alloy Films To Polyimide," Met. Res. Soc. Symp. Proc. Vol. 427, 1996 Materials Research Society, pp. 141-145	
		*Alers, G.B. et al., "Trade-off between reliability and post-CMP defects during recrystallization anneal for copper damascene interconnects," IEEE International Reliability Physics Symposium, Orlando, Florida 2001, pp. 350-354	
		*Gladkikh, A. et. al., "Activation Energy of Electromigration in Copper Thin Film Conductor Lines," Met. Res. Soc. Symp. Proc. 1996 Materials Research Society, pp. 121-133	
		*Russell, S.W. et al., "The Effect of Copper on the Titanium-Silicon Dioxide Reaction and the Implications for Self-Encapsulating, Self-Adhering Metallization Lines," Materials Research Society Symposium Vol 260 - Advanced Metallization and Processing for Semiconductor Devices and Circuits - II (May 1992) pp 763-769	
		*Mel, Yu-Jane et al., "Thermal Stability and Interaction Between Siof and Cu Film," Met. Res. Soc. Symp. Proc. Vol 427, 1996 Materials Research Society, pp. 433-439	

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